TOSHIBA Bipolar Linear Integrated Circuit Silicon Monolithic

TA8126SG,TA8126FG

DC / DC Converter For Electric Tuning (3V USE)

The TA8126SG,TA8126FG are DC /DC converter ICs, which are designed for biasing varactor diodes of tuner system. Those items are especially suitable for supplying high voltage (about $15 \mbox{V}\,/$ 30V) for electric tuning (FM / TV / UHF / AM) system of headphone stereos, radio cassette recorders, or other equipments.

Features

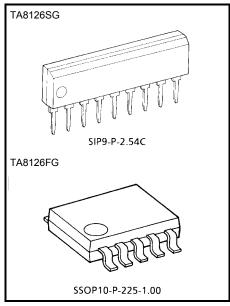
- Excellent regulatory capability of output voltage against fluctuation of supply voltage, and of ambient temperature.
- Excellent spurious radiation by oscillation of sine wave.
- Output voltage can be switched over to 15V or 30V by one-make switch, and is applicable to 10V, too.
- · Few external parts.
- Low supply current (at non-load, VCC = 3V, Ta = 25°C)

 $I_{CCQ1} = 2.4 \text{mA} \text{ (typ., VO} = 15 \text{V mode)}$

 $I_{CCQ2} = 3.0 \text{mA (typ., V}_{O} = 30 \text{V mode})$

Operating supply voltage range (Ta = 25°C) V_{CC1 (opr)} = 1.8~10V, (V_O = 15V mode)

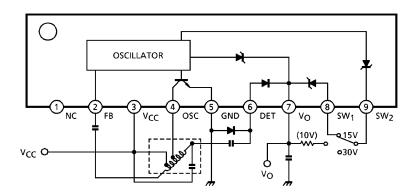
VCC2 (opr) = 2.0~10V, (VO = 30V mode)



Weight SIP9-P-2.54C: 0.72g (typ.) SSOP10-P-225-1.00: 0.09g (typ.)

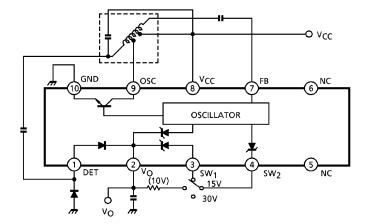
Block Diagram

TA8126SG



Block Diagram

TA8126FG



Terminal Explanation Terminal Voltage with Test Cirucuit ($V_{CC} = 3V$, Ta = 25°C)

| | o. SG / FG n Name | Contents | Equivalent | Terminal Voltage (V) |
|--------------|----------------------|---|---|----------------------------|
| 1/ 6 | NC | _ | _ | _ |
| 2/7 | FB | • Hartley type oscillator $f_{OSC} = \frac{1}{2\pi\sqrt{L_3 C_2}}$ | $\begin{array}{c ccccccccccccccccccccccccccccccccccc$ | 1.4 |
| 4/9 | osc | Controlling oscillation current at the terminal of FB | V _{CC} | 3.0 |
| 3/8 | V _{CC} | _ | _ | 3.0 |
| 5 / 10 | GND | _ | _ | 0 |
| 6 / 1 | DET | Boosted output (voltage double rectifier) | V ₀ O + | _ |
| 7/2 | Vo | V _O = 15V / 30V | 7/2 6/1 DET U3 4/9 OSC | _ |
| 8/3 | SW ₁ | | 7/2 V _O | 1 |
| 9/4 | SW ₂ | Output voltage mode Switchover ON: V _O = 15V OFF: V _O = 30V | DC feed back SW ₂ SW ₂ | - |
| - / 5 | NC | _ | _ | _ |

Application Note

- These ICs have the output voltage by means of boosting the oscillation voltage, derived from hartley type oscillator circuit and of voltage-double rectifier with C₃, D₁, and D₂.
 - (1) Designing of oscillation frequency

$$f_{OSC} \buildrel = \frac{1}{2\pi \sqrt{L_3 \; C_2}}$$

(2) Coil turns can be designed as following: VOSC(p-p) = 2 (VCC(min) - VCE1(sat))

$$n = \frac{n_3}{n_2} = \frac{V_O}{V_{OSC (p-p)}}$$

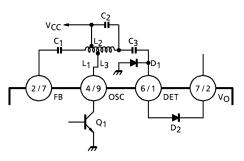


Fig.1 Oscillator and voltage-double

(Note) V_{CC (min)}: Minimum of supply voltage designed by a equipment

 $\begin{array}{lll} V_{CE1 \; (sat)} \!\!: & \text{Saturation voltage of } Q_1 \\ n & : \text{Coil turns ratio } (L_2, L_3) \\ V_O & : \text{Output voltage } (V_O \!\! = \!\! 30V) \end{array}$

The turn of L_1 is designed, so as to make the terminal of FB be about $200 \sim 300 mV_{p-p}$ through C_1 . The turn of L_1 should be small, and the capacitance of C_1 and Q_0 of coil should be large, for the oscillation start at turnig power–on.

- (3) Allowance is advisable for coil design of n, Q_0 . However, spurious radiation can be reduced, in case that the output current and n of coil don't make large.
- 2. In case that spurious radiation due to the oscillation is large, it is recommended to provide LC filter on the power supply line as shown in Fig.2. As for this value, select the optimum one depending on the kind of set.

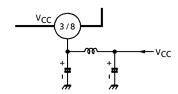


Fig.2 LC Filter

(/): TA8126SG/FG

3. Pattern diagram

The Fig.3 shows the oscillation loop. This pattern diagram should be small, because spurious radiation due to the oscillation is reduced. The Fig.4 shows the rectifier loop. This pattern diagram should be of the small, because spurious radiation due to the switching rectifier is reduced. The two loops should be isolated from other DC lines.

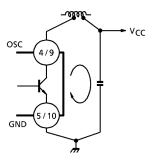


Fig.3 Oscillation loop

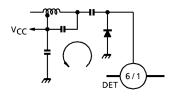


Fig.4 Rectifier loop

 SW_2

Fig.5 Output voltage application



4. Output voltage application

The output voltage is applicable to about 10V, too, in case of connecting to external resistance " $R_{\text{X}}=30k\Omega$ ", as Fig.5. But, in this application, the regulatory circuit doesn't operate, which is against fluctuation of supply voltage and of ambient temperature.

Maximum Ratings (Ta = 25°C)

| Characteris | stic | Symbol | Rating | Unit | |
|-----------------------|----------|-----------------------|---------|------|--|
| Supply voltage | | V _{CC} | 12 | ٧ | |
| Output voltage | | Vo | 35 | V | |
| Power dissipation | TA8126SG | P _D (Note) | 750 | mW | |
| rower dissipation | TA8126FG | FD (Note) | 400 | | |
| Operation temperature | | T _{opr} | -25~75 | °C | |
| Storage temperature | | T _{stg} | -55~150 | °C | |

(Note) Derated above Ta = 25° C in the proportion of 6mW / $^{\circ}$ C for TA8126SG, and of 3.2mW / $^{\circ}$ C for TA8126FG.

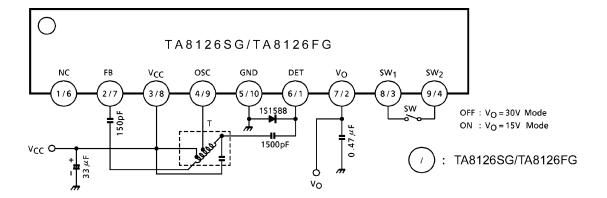
Electrical Characteristics

(unless otherwise specified: V_{CC} = 3V, Ta = 25°C, f_{OSC} = 3.0MHz, I_{O} = 100 μ A)

| Characteristic | Symbol | Test Cir– cuit | SW Mode | Test Condition | Min. | Тур. | Max. | Unit | |
|--|---------------------|--|------------|--|------|------|------|---------|--|
| Supply current | I _{CCQ1} | _ | ON | I _O = 0 | | 2.4 | 5 | mA | |
| оприу синсти | I _{CCQ2} | _ | OFF | I _O = 0 | _ | 3 | 6 | | |
| Boosted output voltage 1 | V _{O1} | _ | ON | | 14.0 | 15.1 | 16.0 | V | |
| V _{O1} supply voltage fluctuation | ΔV _{O1} | _ | ON | V _{CC} = 10V→1.8V | -20 | 0 | 20 | mV | |
| V _{O1} ambient temperature coefficient | V _{O1} / T | _ | ON | Ta = −25~75°C | | ±0.3 | | mV / °C | |
| V _{O1} maximum output current | I _{O1MAX} | _ | ON | ΔV_{O1} = 30mV, with respect to standard I_{O} = 100 μ A | 300 | - | _ | μΑ | |
| Boosted output voltage 2 | V _{O2} | _ | OFF | | 28.0 | 30.3 | 32.5 | V | |
| V _{O2} supply voltage | ΔV _{O2a} | _ | OFF | V _{CC} = 10V→2.5V | -20 | 0 | 20 | - mV | |
| fluctuation | ΔV_{O2b} | _ | OFF | V _{CC} = 4.5V→2.0V | -30 | 0 | 20 | | |
| V _{O2} ambient temperature coefficient | V _{O2} / T | _ | OFF | Ta = −25~75°C | | ±0.3 | _ | mV / °C | |
| | | ΔV_{O2} = 30mV, with respect to standard I_O = 100 μ A | 300 | _ | _ | μΑ | | | |

5 2004-10-12

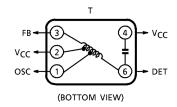
Test Circuit



Coil Data (test circuit)

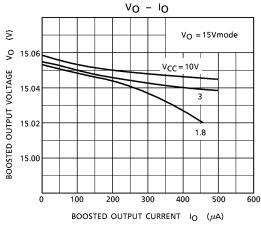
| Test Frequency | L (µH) | Q ₀ | C ₀ (pF) | Turn | | Turn | | Reference |
|-------------------|--------|----------------|---------------------|------|-----|-----------------|---------|-------------------|
| | 2- | -6 | 4–6 | 1–2 | 2–3 | 4–6 | (mmφ) | Reference |
| 3MHz | 103 | 40 | 22 | 7 | 2 | $57\frac{1}{2}$ | 0.1 UEW | (S) 4143–3099–356 |

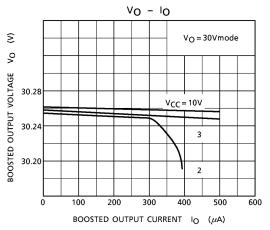
(S): SUMIDA ELECTRIC & Co., Ltd.

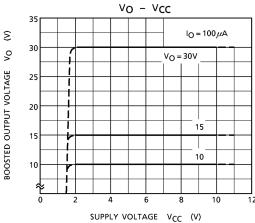


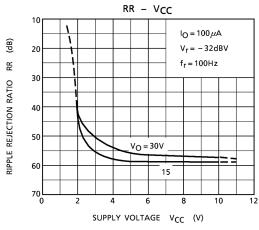
Characteristic Curves

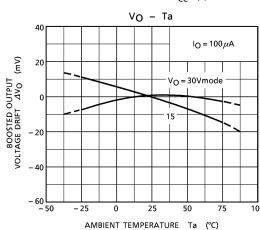
(unless otherwise specified, V_{CC} = 3V, Ta = 25°C, f_{OSC} = 3MHz, I_{O} = 100 μ A)

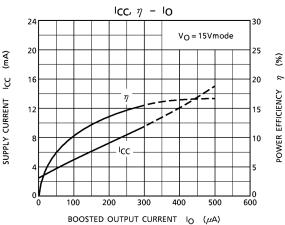




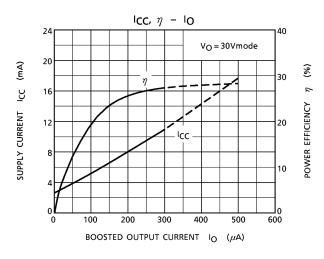


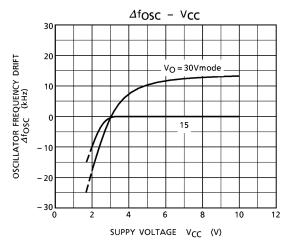


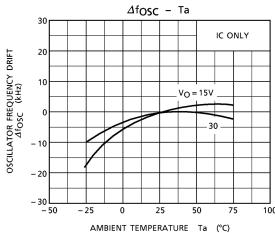




7 2004-10-12





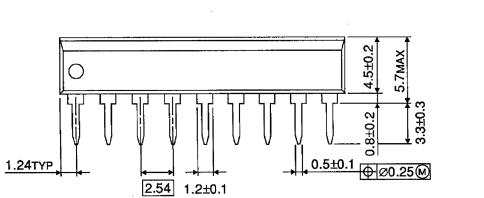


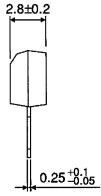
8 2004-10-12

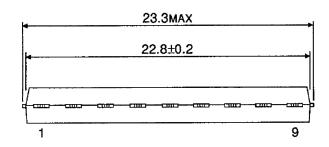
Package Dimensions

SIP9-P-2.54C

Unit: mm





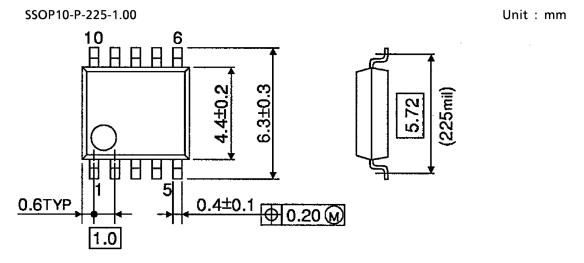


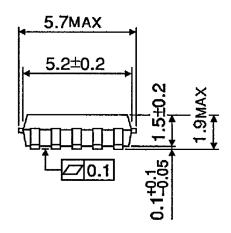
Weight: 0.72g (typ.)

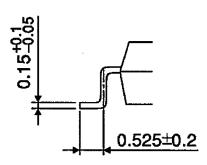
2004-10-12

9

Package Dimensions







Weight: 0.09g (typ.)

About solderability, following conditions were confirmed

- Solderability
 - (1) Use of Sn-63Pb solder Bath
 - solder bath temperature = 230°C
 - · dipping time = 5 seconds
 - · the number of times = once
 - · use of R-type flux
 - (2) Use of Sn-3.0Ag-0.5Cu solder Bath
 - · solder bath temperature = 245°C
 - · dipping time = 5 seconds
 - · the number of times = once
 - · use of R-type flux

RESTRICTIONS ON PRODUCT USE

030619EBA

- The information contained herein is subject to change without notice.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of TOSHIBA or others.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor
 devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical
 stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of
 safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of
 such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
 - In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
- The products described in this document are subject to the foreign exchange and foreign trade laws.
- TOSHIBA products should not be embedded to the downstream products which are prohibited to be produced and sold, under any law and regulations.